# Abstracts

## Foreword (Sep. 1989 [T-MTT])

*J. Goel. "Foreword (Sep. 1989 [T-MTT])." 1989 Transactions on Microwave Theory and Techniques 37.9 (Sep. 1989 [T-MTT] (Special Issue on FET Structures Modeling and Circuit Applications)): 1277-1278.*

Recent advances in GaAs semiconductor material growth, the development of e-beam for submicron lithography, and improved processing techniques have not only improved the performance of conventional field-effect transistors but also resulted in several novel heterostructure devices. At the present time, the focus of the activity in materials is on producing highly uniform and consistent epitaxial layers and improving processing techniques to produce submicron geometries.

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